

# MTL4N47U-MTL4N48U-MTL4N49U

SINGLE CHANNEL OPTOCOUPLER



## Features:

- High Reliability
- Base lead provided for conventional transistor biasing
- Rugged package
- Stability over wide temperature
- +1000V electrical isolation

## Applications:

- Eliminate ground loops
- Level shifting
- Line receiver
- Switching power supplies
- Motor control

## DESCRIPTION

The **MTL4N47U**, **MTL4N48U**, **MTL4N49U** are very high gain optocouplers that utilizes a GaAlAs infrared LED optically coupled to an N-P-N silicon phototransistor packaged in a hermetically sealed 6-pin leadless chip carrier. The 4N47U, 4N48U and 4N49U optocouplers can be supplied to customer specifications as well as tested and screened in accordance with MIL-PRF-19500 to JANTX level.

## ABSOLUTE MAXIMUM RATINGS

Input to Output Voltage.....	+1kV
Emitter-Base Voltage.....	7V
Collector-Emitter Voltage (Value applies to emitter-base open-circuited & the input-diode equal to zero).....	40V
Collector-Base Voltage .....	45V
Reverse Input Voltage .....	2V
Input Diode Continuous Forward Current at (or below) 65°C Free-Air Temperature (see note 1).....	40mA
Peak Forward Input Current (Value applies for $t_{\text{rise}} \leq 1\mu\text{s}$ , PRR < 300 pps).....	1A
Continuous Collector Current.....	50mA
Continuous Transistor Power Dissipation at (or below) 25°C Free-Air Temperature (see Note 2).....	300mW
Storage Temperature .....	-65°C to +125°C
Operating Free-Air Temperature Range .....	-55°C to +100°C
Lead Solder Temperature (10 seconds max.).....	240°C

### Notes:

1. Derate linearly to 125°C free-air temperature at the rate of 0.67 mW/°C above 65°C.
2. Derate linearly to 125°C free-air temperature at the rate of 3 mW/°C.

## RECOMMENDED OPERATING CONDITIONS:

PARAMETER	SYMBOL	MIN	MAX	UNITS
Input Current, Low Level	I <sub>FL</sub>	0	90	µA
Input Current, High Level	I <sub>FH</sub>	2	10	mA
Supply Voltage	V <sub>CE</sub>	5	10	V
Operating Temperature	T <sub>A</sub>	-55	100	°C

## SELECTION GUIDE

PARTNUMBER	PART DESCRIPTION
MTL4N47U.001X	Single Channel Commercial (4N47U) Optocoupler(0° to +70°C operating temperature range)
MTL4N47U.002X	Single Channel Commercial (4N47U) Optocoupler(-40° to +85°C operating temperature range)
MTL4N47U.003X	Single Channel Commercial (4N47U) Optocoupler(-55° to 125°C operating temperature range)
MTL4N47U.004X	Single Channel (4N47U) Optocoupler Screened to JANTX level (-55° to 125°C operating temperature range)
MTL4N48U.001X	Single Channel Commercial (4N48U) Optocoupler(0° to +70°C operating temperature range)
MTL4N48U.002X	Single Channel Commercial (4N48U) Optocoupler(-40° to +85°C operating temperature range)
MTL4N48U.003X	Single Channel Commercial (4N48U) Optocoupler(-55° to 125°C operating temperature range)
MTL4N48U.004X	Single Channel (4N48U) Optocoupler Screened to JANTX level (-55° to 125°C operating temperature range)
MTL4N49U.001X	Single Channel Commercial (4N49U) Optocoupler(0° to +70°C operating temperature range)
MTL4N49U.002X	Single Channel Commercial (4N49U) Optocoupler(-40° to +85°C operating temperature range)
MTL4N49U.003X	Single Channel Commercial (4N49U) Optocoupler(-55° to 125°C operating temperature range)
MTL4N49U.004X	Single Channel (4N49U) Optocoupler Screened to JANTX level (-55° to 125°C operating temperature range)

NOTE: X at end of partnumber represents lead finish Replace with A for gold and S for solder

# MTL4N47U, MTL4N48U, MTL4N49U

SINGLE CHANNEL OPTOCOUPLER

## ELECTRICAL CHARACTERISTICS

$T_A = 25^\circ\text{C}$  unless otherwise specified.

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Input Diode Static Reverse Current	$I_R$			100	$\mu\text{A}$	$V_R = 2\text{V}$	
Input Diode Static Forward Voltage $-55^\circ\text{C}$	$V_F$	1.0		1.7	V	$I_F = 10\text{mA}$	
Input Diode Static Forward Voltage $+25^\circ\text{C}$	$V_F$	0.8		1.5	V	$I_F = 10\text{mA}$	
Input Diode Static Forward Voltage $+100^\circ\text{C}$	$V_F$	0.7		1.3	V	$I_F = 10\text{mA}$	

## OUTPUT TRANSISTOR

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	45			V	$I_C = 100\mu\text{A}, I_B = 0, I_F = 0$	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40			V	$I_C = 1\text{mA}, I_B = 0, I_F = 0$	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	7			V	$I_C = 0\text{mA}, I_E = 100\mu\text{A}, I_F = 0$	
Off-State Collector Current $+25^\circ\text{C}$	$I_C(\text{OFF})$			100	nA	$V_{CE} = 20\text{V}, I_F = 0\text{mA}, I_B = 0$	
	$I_C(\text{OFF})$			100	$\mu\text{A}$	$V_{CE} = 20\text{V}, I_F = 0\text{mA}, I_B = 0$	

## COUPLED CHARACTERISTICS

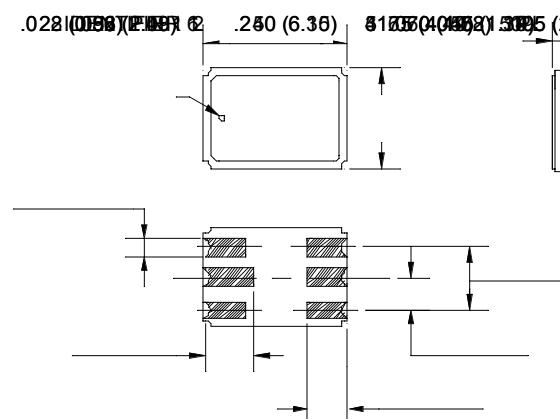
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS	NOTE
On State Collector Current $+25^\circ\text{C}$	$I_C(\text{ON})$	0.5		5	mA	$V_{CE} = 5\text{V}, I_F = 1\text{mA}$	
MTL4N48U		1					
MTL4N49U		2.0		10			
On State Collector Current $+100^\circ\text{C}$	$I_C(\text{ON})$	0.5			mA	$V_{CE} = 5\text{V}, I_F = 2\text{mA}$	
MTL4N48U		1.0					
MTL4N49U		2.0					
On State Collector Current $-55^\circ\text{C}$	$I_C(\text{ON})$	0.7			mA	$V_{CE} = 5\text{V}, I_F = 2\text{mA}$	
MTL4N48U		1.4					
MTL4N49U		2.8					
Collector-Emitter Saturation Voltage	$V_{CE(\text{SAT})}$			0.3	V	$I_F = 2\text{mA}, I_C = 2\text{mA}, I_B = 0$	
Input to Output Internal Resistance	$R_{IO}$	$10^{11}$			$\Omega$	$V_{\text{IN-OUT}} = 500\text{V}$	1
Input to Output Capacitance	$C_{IO}$		2.5	5	pF	$f = 1\text{MHz}, V_{\text{IN-OUT}} = 1\text{kV}$	1
Rise/Fall Time-Phototransistor Operation MTL4N47U	$t_r/t_f$		10	20	$\mu\text{s}$	$V_{CC} = 10\text{V}, I_F = 5\text{mA}, R_L = 100\Omega, I_B = 0$	
MTL4N48U			10	25			
MTL4N49U			10	25			
Rise/Fall Time-Photodiode Operation	$t_r/t_f$			0.85	$\mu\text{s}$	$V_{CC} = 10\text{V}, I_F = 5\text{mA}, R_L = 100\Omega, I_E = 0$	
MTL4N48U				0.85			
MTL4N49U				0.85			

## NOTES:

These parameters are measured between all phototransistor leads shorted together and with both input diode leads shorted together.

This parameter must be measured using pulse techniques ( $t_w = 100\mu\text{s}$  duty cycle  $\leq 1\%$ ).

Package Dimensions



Schematic Diagram

